

Notice of References CitedApplication/Control No.
10/019,540Applicant(s)/Patent Under Reexam
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Savitri MulpuriArt Unit
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NON-PATENT DOCUMENTS

	Include, as applicable: Author, Title, Date, Publisher, Edition or Volume, Pertinent Pages
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* A copy of this reference is not being furnished with this Office action. See MPEP § 707.05(a).

¹ Dates in MM-YYYY format are publication dates.² Classifications may be U.S. or foreign.